ALTERNATIVE TO PTO/SB/08a/b (06-03)

Substitute for form 1449/PTO				Complete if Known	
				Application Number	10/537,804
INFORMATION DISCLOSURE				Filing Date	June 7, 2005
s	TATEMENT I	3Y /	APPLICANT	First Nemed Inventor	Robert DWILINSKI
-				Art Unit	Not yet assigned 1792
1	(Use as many sh	eets a	s necessary)	Examiner Neme	Not yet assigned. /Fellsa Hiteshaw/
Sheet	1	of	1	Attorney Docket Number	204552035400

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	5.306.662	4-26-1994	Nakamura et al.	

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁶ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	┲	
	2.	JP-5-183189	7-23-1993		abstract, also corresponds to U.S. Patent No. 5,306,662		

EXAMINER: Initial information considered, whether or not classion is in conformance with MPEP 609. Draw line through classion if not in conformance act in the considered, include copy of this form with noted communication is epident. **Applicant's unique classion designation market opidional.** See information and the considered product of the conformation and the

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	or Cite No.1 Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the in magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publis and/or country where published.		T ²		
	3.	M. K. Kelly et al. (1996) "Optical Patterning of GaN Films," Appl Phys. Lett 69(12), pp. 1749- 1751			
	4.	W. S. Wong et al. (1999) *Fabrication of Thin-Film InGaN Light-Emitting Diode Membranes By Laser Lift-Off,* Applied Physics Letters 75(10), pp. 1360-1362			
	5.	S. Porowski et al. (1993) "Prospects for High-Pressure Crystal Growth of III-V Nitrides," Inst. Phys. Conf. Ser. No. 137. Chapter 4, pp. 369-372			

^{*}EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Examiner	/Felisa Hiteshew/	Date	04/18/2008
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